

G1270

PNP EPITAXIAL PLANAR TRANSISTOR

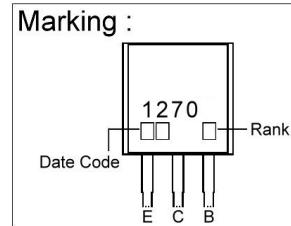
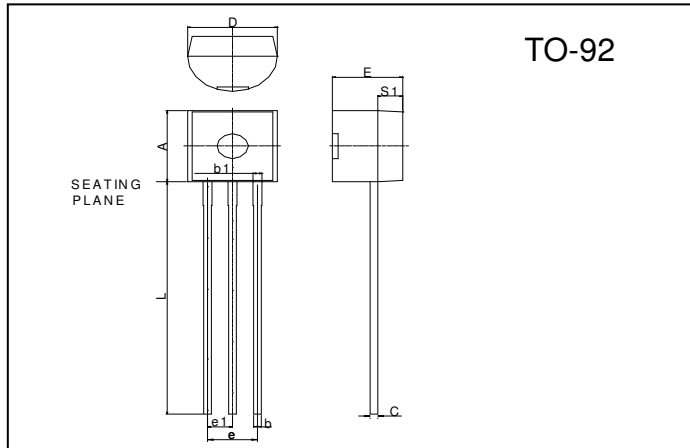
Description

The G1270 is designed for general purpose switching and amplifier applications.

Features

- Excellent $h_{FE}(2)=25(\text{Min.}) @ V_{CE}=-6V, I_C=-400\text{mA}$

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings (TA=25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V _{CB0}	-35	V
Collector to Emitter Voltage	V _{CEO}	-30	V
Emitter to Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-500	mA
Total Device Dissipation	P _D	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

Electrical Characteristics (TA = 25°C unless otherwise noted)

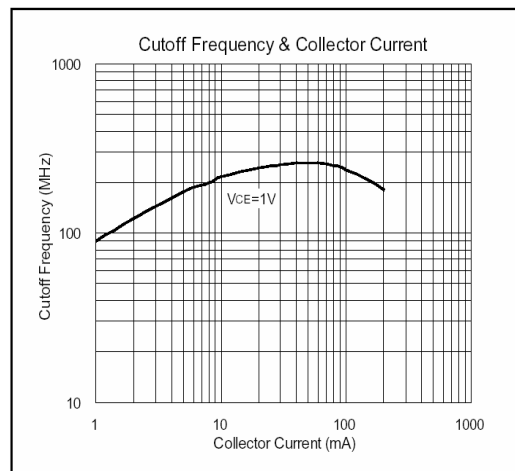
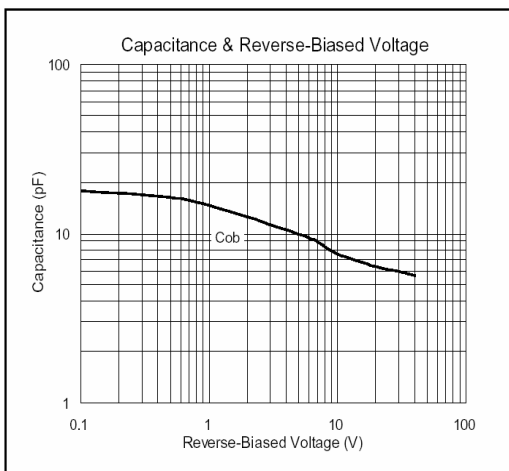
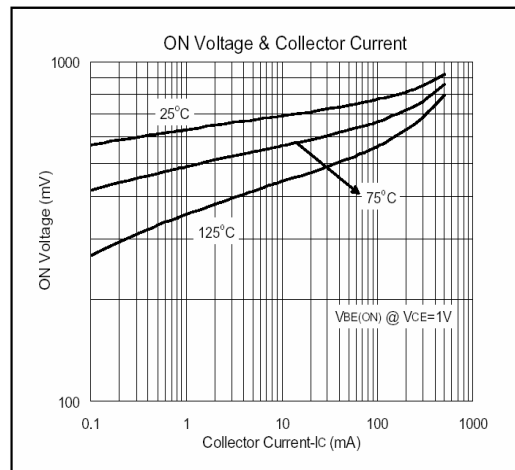
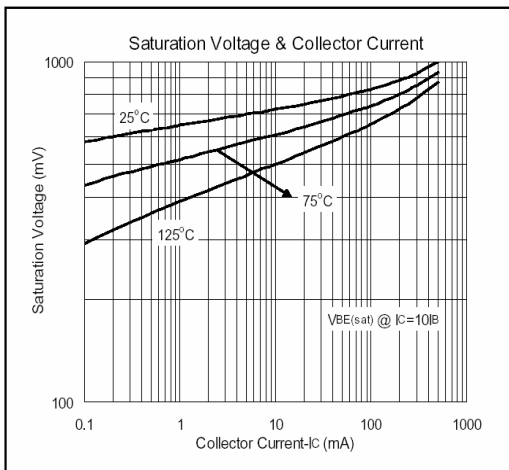
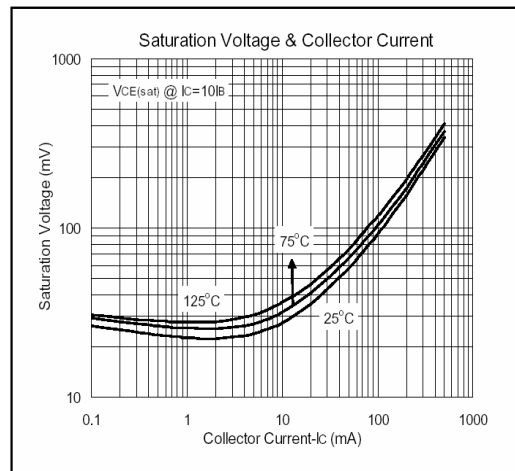
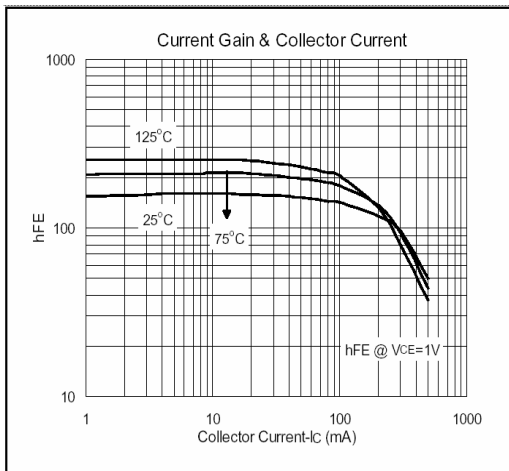
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V _{CB0}	-35	-	-	V	I _C =-100uA, I _E =0
V _{CEO}	-30	-	-	V	I _C =-1mA, I _B =0
V _{EBO}	-5	-	-	V	I _E =-100uA, I _C =0
I _{CB0}	-	-	-100	nA	V _{CB} =-35V, I _E =0
I _{EBO}	-	-	-100	nA	V _{EB} =-5V, I _C =0
*V _{CE(sat)}	-	-	-0.25	V	I _C =-100mA, I _B =-10mA
*V _{BE(on)}	-	-	-1.0	V	V _{CE} =-1V, I _C =-100mA
*h _{FE1}	70	-	240		V _{CE} =-1V, I _C =-100mA
*h _{FE2}	25	-	-		V _{CE} =-6V, I _C =-400mA
f _T	100	-	-	MHz	V _{CE} =-1V, I _C =-10mA, f=100MHz
C _{ob}	-	-	8	pF	V _{CB} =-10V, I _E =0, f=1MHz

*Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification Of h_{FE}

Rank	O	Y
h _{FE1} Range	70 - 140	120 - 240
h _{FE2} Range	Min. 25	Min. 40

Characteristics Curve



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